

## CSM4435SOP8

### 30V P-Channel Enhancement Mode MOSFET

**Voltage**

**-30 V**

**Current**

**-8A**

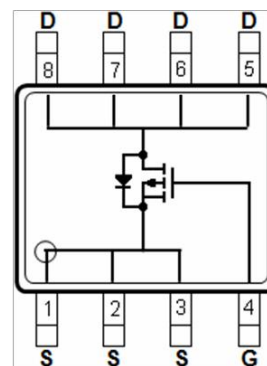
#### Features

- $R_{DS(ON)}$ ,  $V_{GS}@-10V$ ,  $I_D@-8A < 15.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-6A < 20m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance

#### Mechanical Data

- Case: SOP-8 package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams

SOP-8



### Maximum Ratings and Thermal Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_A=25^{\circ}C$	$I_D$	-8	A
	$T_A=70^{\circ}C$		-6	
Pulsed Drain Current (Note 1)		$I_{DM}$	-32	
Power Dissipation	$T_A=25^{\circ}C$	$P_D$	1.7	W
	$T_A=70^{\circ}C$		1.1	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^{\circ}C$
Typical Thermal Resistance Junction to Ambient (Note 5)		$R_{\theta JA}$	73.5	$^{\circ}C/W$

## CSM4435SOP8

### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.6	-2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A	-	12	15.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	-	17	20	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-8A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	14	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.6	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	5.4	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1556	-	pF
Output Capacitance	C <sub>oss</sub>		-	243	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	175	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 1,2)	-	7.3	-	ns
Turn-On Rise Time	tr		-	13	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	88	-	
Turn-Off Fall Time	tf		-	48	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>s</sub>	---	-	-	-10	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>s</sub> =-1A, V <sub>GS</sub> =0V	-	-0.7	-1.0	V

#### NOTES :

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}\text{C}$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J=25^{\circ}\text{C}$ .
5.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

## CSM4435SOP8

### TYPICAL CHARACTERISTIC CURVES

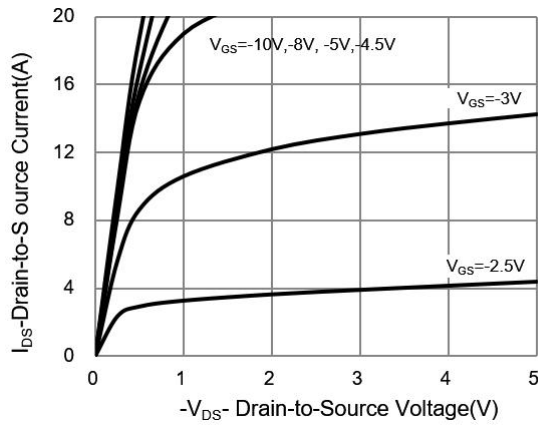


Fig.1 On-Region Characteristics

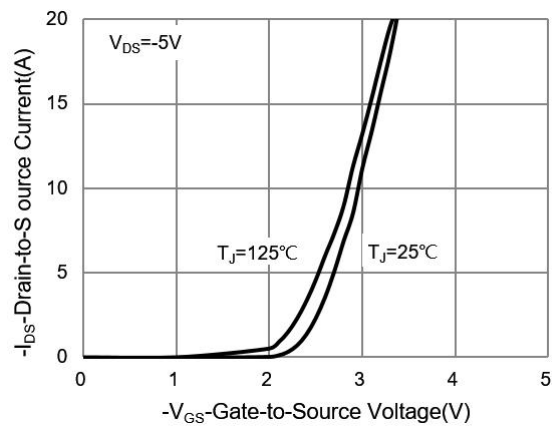


Fig.2 Transfer Characteristics

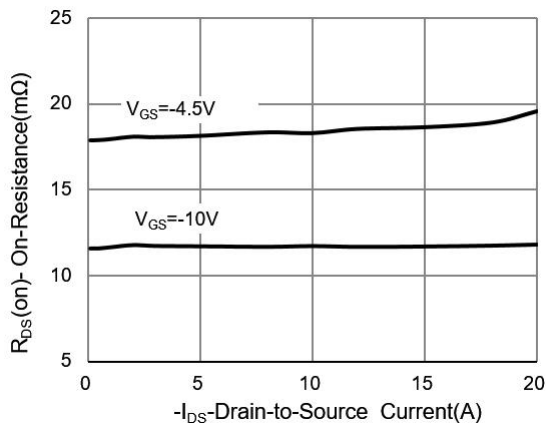


Fig.3 On-Resistance vs. Drain Current

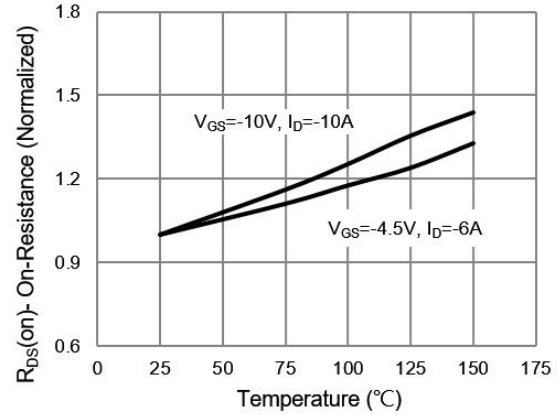


Fig.4 On-Resistance vs. Junction temperature

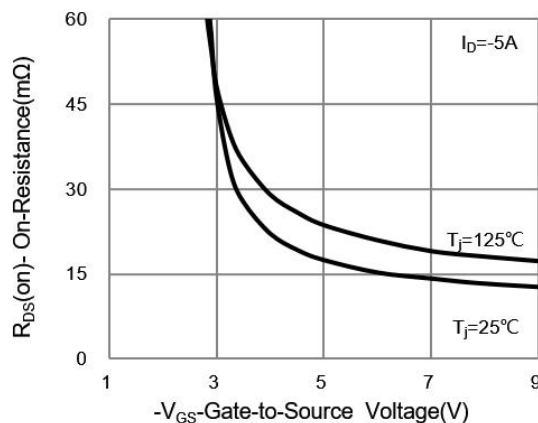


Fig.5 On-Resistance Variation with VGS.

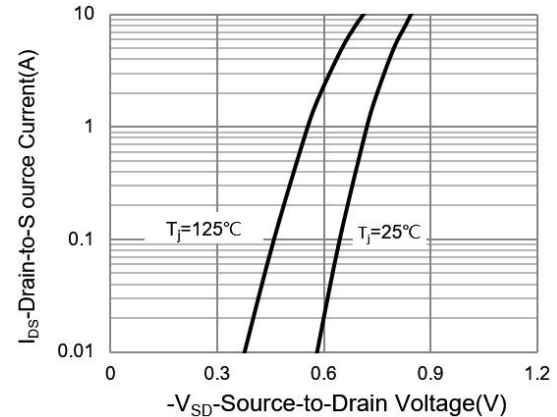


Fig.6 Body Diode Characteristics

## CSM4435SOP8

### TYPICAL CHARACTERISTIC CURVES

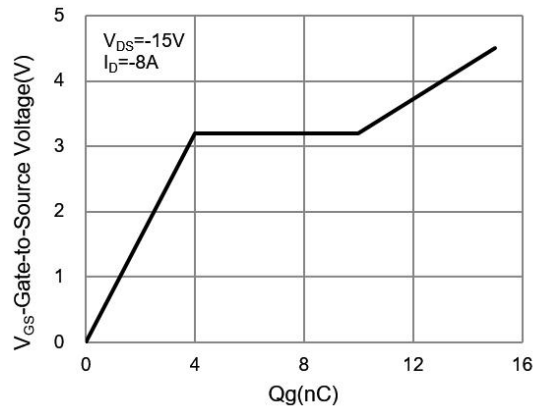


Fig.7 Gate-Charge Characteristics

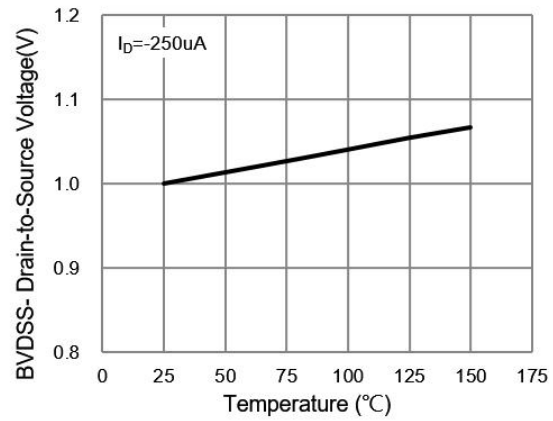


Fig.8 Breakdown Voltage Variation vs. Temperature

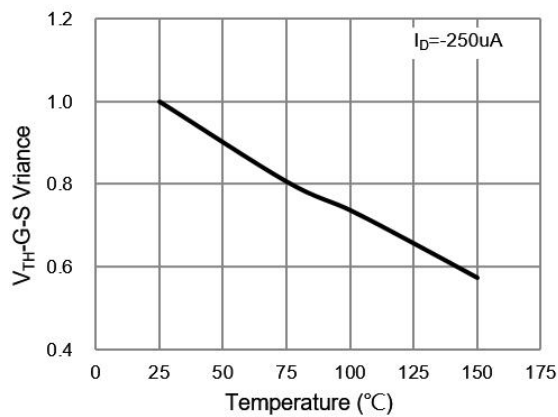


Fig.9 Threshold Voltage Variation with Temperature.

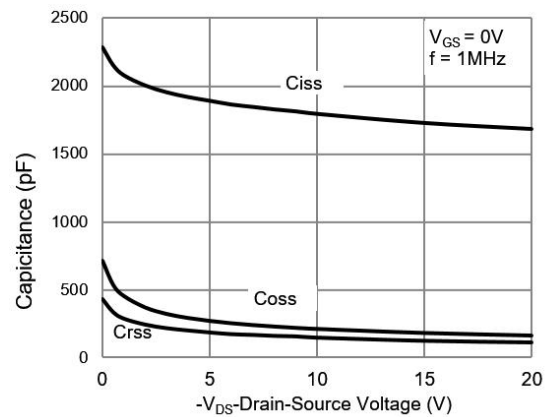


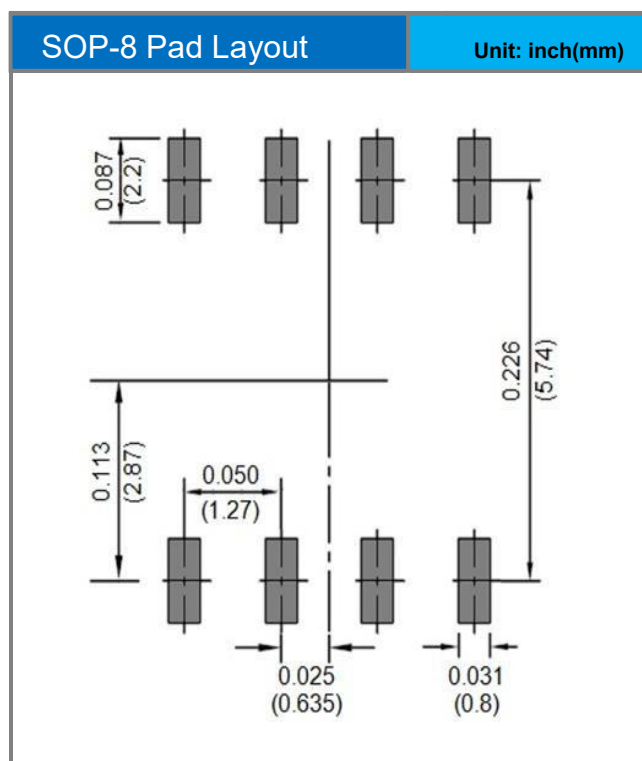
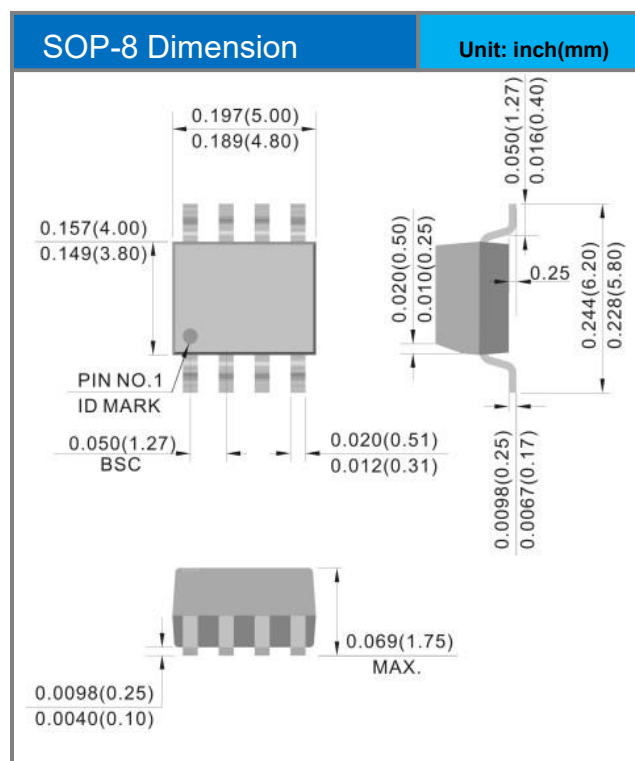
Fig.10 Capacitance vs. Drain-Source Voltage.

## CSM4435SOP8

### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type
CSM4435SOP8	SOP-8	3K / reel

### Packaging Information & Mounting Pad Layout



## **CSM4435SOP8**

### **Notice**

Specifications of the products displayed herein are subject to change without notice. CCS or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in CCS terms and conditions of sale for such products, CCS assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of CCS products including liability or warranties relating to fitness for a particular purpose, merchant ability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications.

Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CCS for any damages resulting from such improper use or sale.